



ELECTRONICS, INC.  
 44 FARRAND STREET  
 BLOOMFIELD, NJ 07003  
 (973) 748-5089  
<http://www.nteinc.com>

## NTE5511 thru NTE5513 Silicon Controlled Rectifier (SCR) 5 Amp, TO66

**Description:**

The NTE5511 thru NTE5513 all-diffused, three junction, silicon controlled rectifiers (SCR's) are intended for use in power-control and power-switching applications. These devices are available in a TO66 type package and have a blocking voltage capability of up to 600V and a forward current rating of 5A (rms value) at a case temperature of +75°C.

**Features:**

- Designed Especially for High-Volume Systems
- Readily Adaptable for PC Boards and Metal Heat Sinks
- Low Switching Losses
- High di/dt and dv/dt Capabilities
- Shorted Emitter Gate-Cathode Construction
- Forward and Reverse Gate Dissipation Ratings
- All-Diffused Construction Assures Exceptional Uniformity and Stability of Characteristics
- Direct-Soldered Internal Construction Assures Exceptional Resistance to Fatigue
- Symmetrical Gate-Cathode Construction Provides Uniform Current Density, Rapid Electrical Conduction, and Efficient Heat Dissipation
- All-Welded Construction and Hermetic Sealing
- Low Leakage Currents, Forward and Reverse
- Low Forward Voltage Drop at High Current Levels
- Low Thermal Resistance

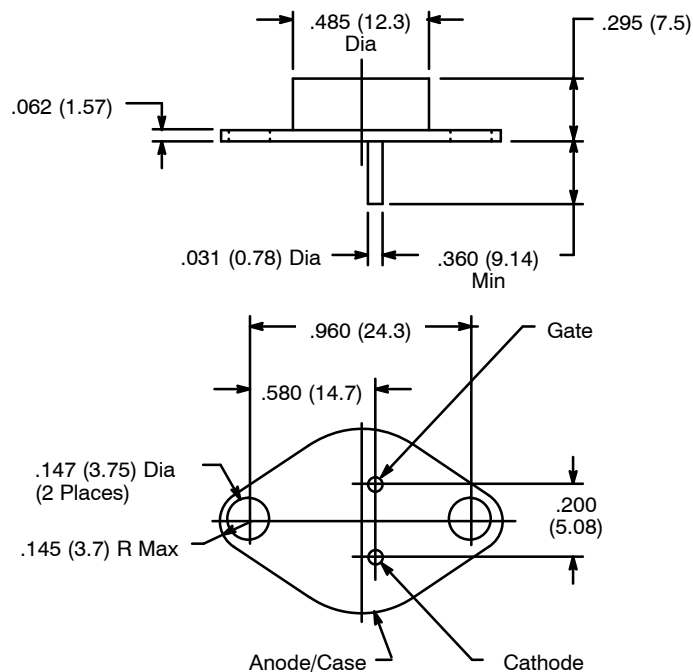
**Absolute Maximum Ratings:** (For Operation with Sinusoidal AC Supply Voltage at a Frequency between 50Hz and 400Hz, and with Resistive or Inductive Load)

Transient Peak Reverse Voltage (Non-Repetitive), $V_{RM}$ (non-rep)	
NTE5511 .....	330V
NTE5512 .....	660V
NTE5513 .....	700V
Peak Reverse Voltage (Repetitive), $V_{RM}$ (rep)	
NTE5511 .....	200V
NTE5512 .....	400V
NTE5513 .....	600V
Peak Forward Blocking Voltage (Repetitive), $V_{FBOM}$ (rep)	
NTE5511 .....	600V
NTE5512 .....	600V
NTE5513 .....	700V
Average DC Forward Current, $I_{F(av)}$ ( $T_C = +75^\circ C$ mounted on heat sink, conduction angle or $180^\circ$ ) .....	
	3.2A
RMS Forward Current ( $T_C = +75^\circ C$ mounted on heat sink), $I_{FRMS}$ .....	
	5A
Peak Surge Current (For one cycle of applied voltage), $i_{FM(surge)}$ .....	
	60A
Sub-Cycle Surge (Non-Repetitive, for a period of 1ms to 8.3ms), $I^2t$ .....	
	15A <sup>2</sup> sec
Rate of Change of Forward Current (Note 1), di/dt .....	
	200A/ $\mu$ s
Gate Power (Peak, Forward, or Reverse, for 10 $\mu$ s duration, Note 2), $P_{GM}$ .....	
	13W
Average Gate Power (Note 2), $P_{GAV}$ .....	
	500mW
Operating Case Temperature Range, $T_C$ .....	
	-40° to +100°C
Storage Temperature Range, $T_{stg}$ .....	
	-40° to +125°C

Note 1.  $V_{FB} = V_{BOO}$ (min value),  $I_{GT} = 200mA$ , 0.5 $\mu$ s rise time  
 Note 2. Any values of peak gate current or peak gate voltage to give the maximum gate power is permissible.

**Electrical Characteristics:** (At Maximum Ratings,  $T_C = +25^\circ\text{C}$  unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit	
Forward Breakover Voltage NTE5511	$V_{BOO}$	$T_C = +100^\circ\text{C}$	200	-	-	V	
NTE5512			400	-	-	V	
NTE5513			600	-	-	V	
Peak Blocking Forward Current NTE5511	$I_{FBOM}$	$V_{FBO} = 200\text{V}$	$T_C = +100^\circ\text{C}$	-	0.10	1.5	mA
NTE5512		$V_{FBO} = 400\text{V}$		-	0.20	3.0	mA
NTE5513		$V_{FBO} = 600\text{V}$		-	0.40	4.0	mA
Peak Blocking Reverse Current NTE5511	$I_{RBOM}$	$V_{RBO} = 200\text{V}$	$T_C = +100^\circ\text{C}$	-	0.05	0.75	mA
NTE5512		$V_{RBO} = 400\text{V}$		-	0.10	1.5	mA
NTE5513		$V_{RBO} = 600\text{V}$		-	0.20	2.0	mA
Forward Voltage Drop	$V_F$	$I_F = 30\text{A}$	-	2.15	2.80	V	
DC Gate-Trigger Current	$I_{GT}$		-	8	15	mA	
DC Gate-Trigger Voltage	$V_{GT}$		-	1.2	2.0	V	
Holding Current	$I_{Hold}$		-	10	20	mA	
Critical Rate of Applied Forward Voltage	$dv/dt$	$V_{FB} = v_{BOO}$ (min), exponential rise, $T_C = +100^\circ\text{C}$	10	200	-	V/ $\mu\text{s}$	
Turn-On Time (Delay Time + Rise Time)	$t_{on}$	$V_{FB} = v_{BOO}$ (min), $i_F = 4.5\text{A}$ , $I_{GT} = 200\text{mA}$ , $0.1\mu\text{s}$ rise time	0.75	1.5	-	$\mu\text{s}$	
Turn-Off Time (Reverse Recovery Time + Gate Recovery Time)	$t_{off}$	$i_F = 2\text{A}$ , $50\mu\text{s}$ pulse width, $dv_{FB}/dt = 20\text{V}/\mu\text{s}$ , $di_r/dt = 30\text{A}/\mu\text{s}$ , $I_{GT} = 200\text{mA}$ , $T_C = +75^\circ\text{C}$	-	15	50	$\mu\text{s}$	
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$		-	-	4	$^\circ\text{C}/\text{W}$	



## X-ON Electronics

Largest Supplier of Electrical and Electronic Components

*Click to view similar products for [SCRs](#) category:*

*Click to view products by [NTE](#) manufacturer:*

Other Similar products are found below :

[NTE5428](#) [NTE5448](#) [NTE5457](#) [NTE5511](#) [T1500N16TOF VT](#) [T720N18TOF](#) [T880N14TOF](#) [T880N16TOF](#) [TN1205H-6G](#) [TN1215-800B-TR](#)  
[TS110-7UF](#) [TT104N12KOF-A](#) [TT104N12KOF-K](#) [TT162N16KOF-A](#) [TT162N16KOF-K](#) [TT330N16AOF](#) [VS-111RKI120PBF](#) [VS-16RIA100](#)  
[VS-22RIA20](#) [VS-2N5206](#) [VS-2N685](#) [VS-40TPS08A-M3](#) [VS-50RIA10](#) [057219R](#) [T1190N16TOF VT](#) [T1220N22TOF VT](#) [T201N70TOH](#)  
[T830N14TOF](#) [T830N18TOF](#) [TD92N16KOF-A](#) [TT250N12KOF-K](#) [VS-ST180S12P0V](#) [VS-25RIA40](#) [VS-16RIA120](#) [VS-30TPS08PBF](#)  
[TN1215-800G-TR](#) [NTE5427](#) [NTE5442](#) [X0405NF 1AA2](#) [VS-ST300S20P0PBF](#) [T2160N28TOF VT](#) [TT251N16KOF-K](#) [VS-22RIA100](#) [VS-](#)  
[16RIA40](#) [CR02AM-8#F00](#) [VS-ST110S12P0VPBF](#) [TD250N16KOF-A](#) [GA301A](#) [VS-ST110S16P0](#) [VS-10RIA10](#)